



# 60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI3333-8 (SWP) (TYPE UX)

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>C</sub> = +25°C
60V	9.5mΩ @ V <sub>GS</sub> = 10V	45.4A
	13.3mΩ @ V <sub>GS</sub> = 4.5V	38.4A

#### **Features**

- Rated to +175°C—Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production— Ensures More Reliable and Robust End Application
- Low On-Resistance
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMTH69M8LFVWQ</u>)

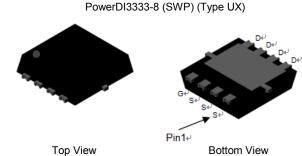
### **Description and Applications**

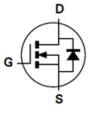
This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8 (SWP) (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)





**Equivalent Circuit** 

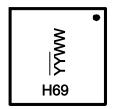
#### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMTH69M8LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2000/Tape & Reel
DMTH69M8LFVW-13	PowerDI3333-8 (SWP) (Type UX)	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



H69 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 19 = 2019)
WW = Week Code (01 to 53)

July 2019



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	60	V	
Gate-Source Voltage	$V_{GSS}$	±16	V	
Continuous Drain Current (Note 5) // = 10)/	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	l <sub>D</sub>	45.4 32.1	Α
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	T <sub>A</sub> = +25°C T <sub>A</sub> = +100°C	Ι <sub>D</sub>	15.9 11.2	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	180	Α	
Maximum Continuous Body Diode Forward Current (Note 5)	Is	45	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	180	Α	
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	30	Α	
Avalanche Energy, L = 0.1mH	E <sub>AS</sub>	45	mJ	

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5) $T_A = +25^{\circ}C$		$P_{D}$	3.6	W
Thermal Resistance, Junction to Ambient (Note 5)		R <sub>OJA</sub>	41.7	°C/W
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		$P_{D}$	29.4	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	5.1	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

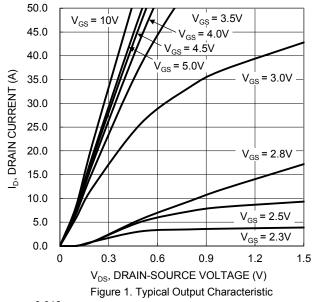
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_		1	μΑ	V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V	
Gate-Source Leakage		_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	7.7	9.5	mΩ	$V_{GS} = 10V, I_D = 13.5A$	
Static Dialit-Source Off-Resistance	R <sub>DS(ON)</sub>	_	9.5	13.3	mΩ	$V_{GS} = 4.5V, I_D = 11.5A$	
Diode Forward Voltage	$V_{SD}$	_	8.0	1.2	V	$V_{GS} = 0V, I_{S} = 13.5A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	_	1925	_	pF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, -f = 1MHz	
Output Capacitance	Coss	_	438	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	41	_	рF		
Gate Resistance	Rg	_	1.7	_	Ω	$V_{DS}$ = 0V, $V_{GS}$ = 0V, f = 1MHz	
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$	_	33.5	_	nC		
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_g$	_	15.6	_	nC	V <sub>DS</sub> = 30V, I <sub>D</sub> = 13.5A	
Gate-Source Charge	Q <sub>gs</sub>	_	4.7	_	nC	VDS = 30V, ID = 13.5A	
Gate-Drain Charge	$Q_{gd}$	_	5.3	_	nC	1	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	4.5	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $R_{G} = 6\Omega, I_{D} = 13.5A$	
Turn-On Rise Time	t <sub>R</sub>	_	8.6	_	ns		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	35.9	_	ns		
Turn-Off Fall Time	t <sub>F</sub>		15.7	_	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	18.2	_	ns	$I_{\rm c} = 13.5\Delta$ di/dt = $400\Delta/\mu c$	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	33.1	_	nC		

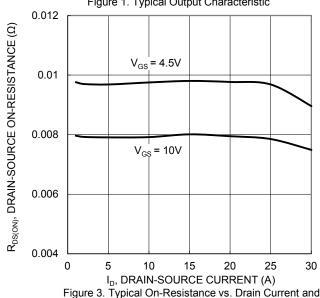
Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  6. Thermal resistance from junction to soldering point (on the exposed drain pad).
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.



### DMTH69M8LFVW





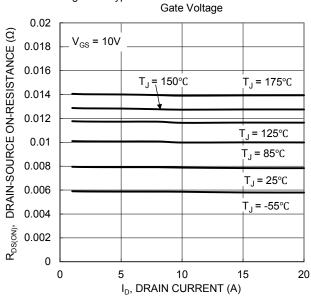
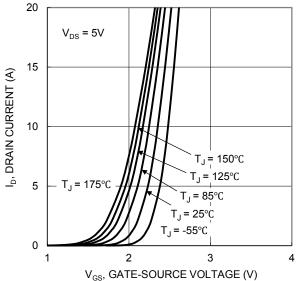
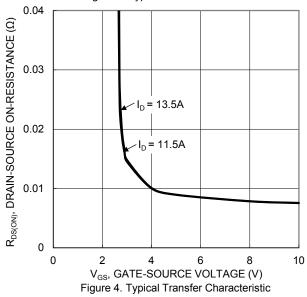


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic



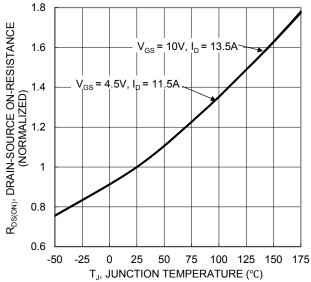
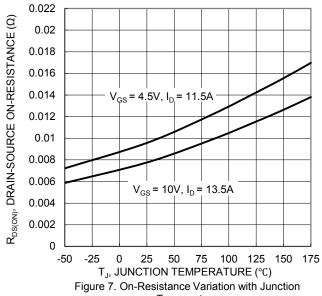


Figure 6. On-Resistance Variation with Junction Temperature







Temperature

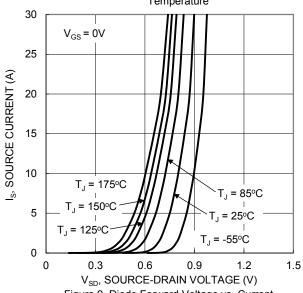
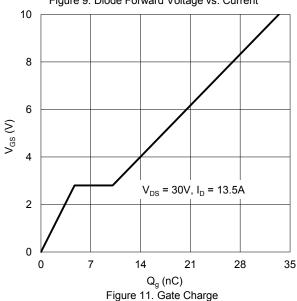
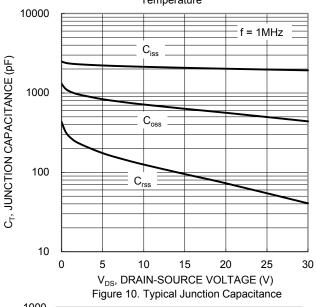


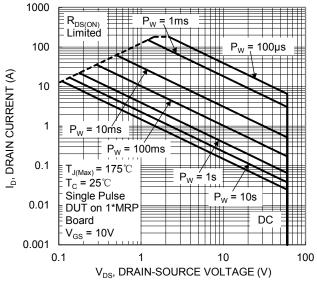
Figure 9. Diode Forward Voltage vs. Current



3  $V_{GS(TH)}$ , GATE THRESHOLD VOLTAGE (V) 2.5 2  $I_D = 1 \text{mA}$ 1.5 1  $I_D = 250 \mu A$ 0.5 0 -25 50 75 100 125 150 175 0 25 -50 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

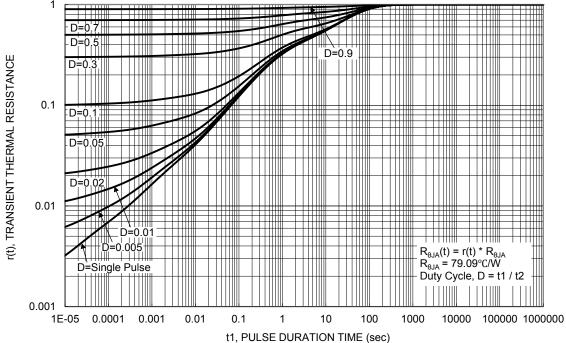
Figure 8. Gate Threshold Variation vs. Junction Temperature





July 2019



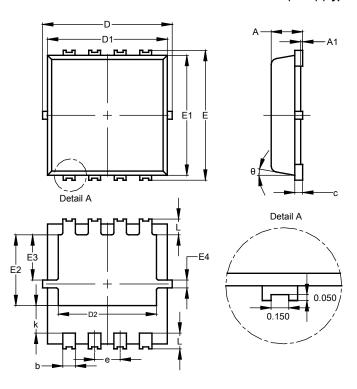




### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8 (SWP) (Type UX)

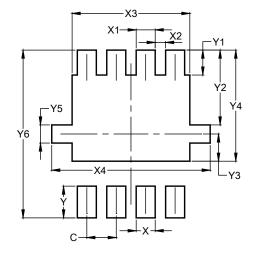


PowerDI3333-8 (SWP)						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
<b>A</b> 1	0.00	0.05				
þ	0.25	0.40	0.32			
C	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
П	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
<b>E</b> 3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
Ф			0.65			
k	0.50	0.90	0.70			
Т	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)				
С	0.650				
Х	0.420				
X1	0.420				
X2	0.230				
Х3	2.600				
X4	3.500				
Υ	0.700				
Y1	0.550				
Y2	1.650				
Y3	0.600				
Y4	2.450				
Y5	0.400				
Y6	3.700				



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